

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	2	jp-2000243856-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:40
2	BRS	2	jp-2002246480-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:40
3	BRS	398	first adj gate adj dielectric and second adj gate adj dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:41
4	BRS	263	first adj gate adj dielectric with second adj gate adj dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:41
5	BRS	26	first adj gate adj dielectric with second adj gate adj dielectric and gate adj dielectric with anneal\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:43
6	BRS	25	first adj gate adj dielectric with second adj gate adj dielectric and gate adj dielectric with anneal\$3 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:43
7	BRS	65	gate adj dielectric with anneal\$3 near2 rapid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:45
8	BRS	4	gate adj dielectric near2 anneal\$3 near2 rapid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:44
9	BRS	16	gate adj dielectric near5 anneal\$3 near2 rapid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:44
10	BRS	2	"5783469".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:45
11	BRS	0	gate adj dielectric with thermal with oxidization with wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:46

12	BRS	10	gate adj dielectric with thermal with oxidization	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 18:58
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	Type	Hits	Search Text	DBs	Time Stamp
13	BRS	2	"6525380".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:47
14	BRS	26	gate adj dielectric with thermal with wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/12 20:47
15	BRS	0	gate adj dielectric with thermal with oxidization with wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 18:59
16	BRS	74	thermal with oxidization with wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 18:59
17	BRS	20	thermal with oxidization with wet with gate with (dielectric or insulat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 18:59
18	BRS	29	thermal with oxidization with wet with gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 19:04
19	BRS	39	thermal near3 oxidization near3 wet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 19:08
20	BRS	14	thermal near3 oxidization near3 wet and isolat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 19:13
21	BRS	38	thermal near3 oxidiz\$5 near3 wet and isolat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 19:13
22	BRS	1017	438/151.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 20:30
23	BRS	69	438/219.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 20:31
24	BRS	857	438/275.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/11/13 20:31

	Type	Hits	Search Text	DBs	Time Stamp
25	BRS	370	438/279.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	2004/11/13 20:31
26	BRS	963	438/287.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	2004/11/13 20:31
27	BRS	1092	438/585.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	2004/11/13 20:31
28	BRS	491	438/981.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	2004/11/13 20:31